

BSS84AKM

50 V, 230 mA P-channel Trench MOSFET Rev. 1 — 23 May 2011

Product data sheet

Product profile 1.

1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small SOT883 (SC-101) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- ESD protection up to 1 kV
- AEC-Q101 qualified

1.3 Applications

- Relay driver
- High-speed line driver

- High-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	-50	V
V_{GS}	gate-source voltage			-20	-	20	V
I_D	drain current	V_{GS} = -10 V; T_{amb} = 25 °C	[1]	-	-	-230	mΑ
Static characteristics							
R _{DSon}	drain-source on-state resistance	V_{GS} = -10 V; I_{D} = -100 mA; T_{j} = 25 °C		-	4.5	7.5	Ω

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².



2. Pinning information

Table 2. Pinning information

	-			
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	S	source	1 3	
3	D	drain	Transparent top view SOT883 (SOT883)	G S Sym146

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BSS84AKM	SOT883	leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm	SOT883

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
BSS84AKM	ZA

^{[1] % =} placeholder for manufacturing site code

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

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Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-50	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	$V_{GS} = -10 \text{ V}; T_{amb} = 25 \text{ °C}$	<u>[1]</u>	-	-230	mA
		V _{GS} = -10 V; T _{amb} = 100 °C	<u>[1]</u>	-	-150	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-0.9	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	340	mW
			[1]	-	715	mW
		T _{sp} = 25 °C		-	2700	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drai	in diode					
Is	source current	T _{amb} = 25 °C	<u>[1]</u>	-	-230	mA
ESD maxim	um rating					
V _{ESD}	electrostatic discharge voltage	НВМ	[3]	-	1000	V

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

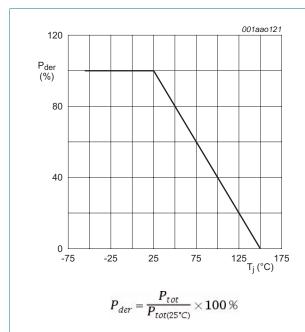


Fig 1. Normalized total power dissipation as a function of junction temperature

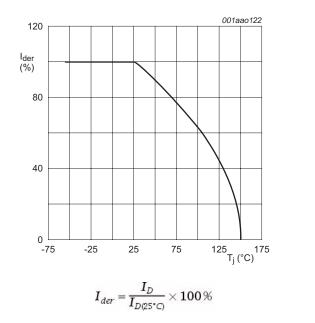
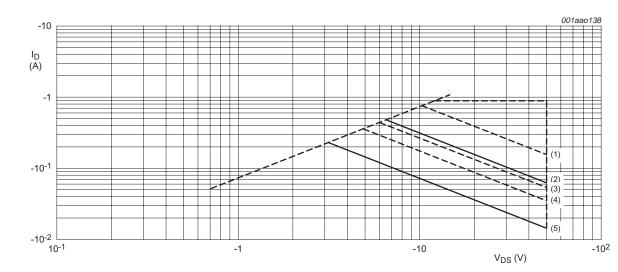


Fig 2. Normalized continuous drain current as a function of junction temperature

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I_{DM} is single pulse

- (1) $t_p = 1 \text{ ms}$
- (2) DC; $T_{sp} = 25 \, ^{\circ}\text{C}$
- (3) $t_p = 10 \text{ ms}$
- (4) $t_p = 100 \text{ ms}$
- (5) DC; $T_{amb} = 25$ °C; drain mounting pad 1 cm²

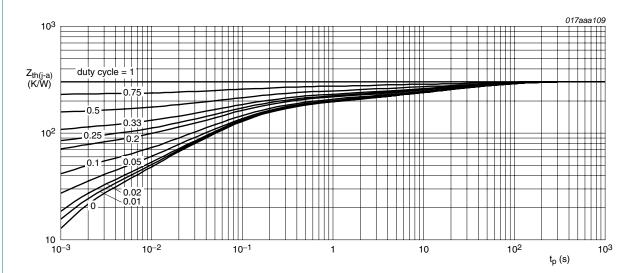
Fig 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

Table 6. Thermal characteristics

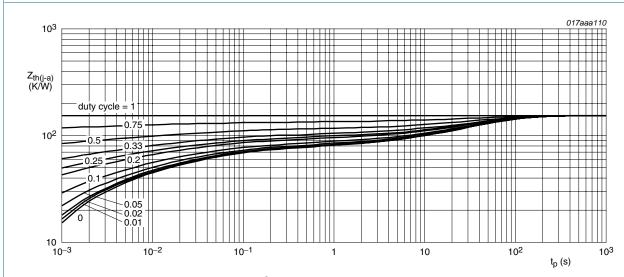
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u> _	310	360	K/W
			[2] _	150	175	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		-	-	40	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².



FR4 PCB, standard footprint

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm²

Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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7. Characteristics

Table 7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	nracteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -10 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-50	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	-1.1	-1.6	-2.1	V
I _{DSS}	drain leakage current	$V_{DS} = -50 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μΑ
		$V_{DS} = -50 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 ^{\circ}\text{C}$	-	-	-2	μΑ
I _{GSS}	gate leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-10	μΑ
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-10	μΑ
R _{DSon}	drain-source on-state resistance	V_{GS} = -10 V; I_{D} = -100 mA; T_{j} = 25 °C	-	4.5	7.5	Ω
		$V_{GS} = -10 \text{ V}; I_D = -100 \text{ mA}; T_j = 150 ^{\circ}\text{C}$	-	8	13.5	Ω
		$V_{GS} = -5 \text{ V}; I_D = -100 \text{ mA}; T_j = 25 \text{ °C}$	-	5.7	8.5	Ω
9 _{fs}	forward transconductance	$V_{DS} = -10 \text{ V}; I_D = -100 \text{ mA}; T_j = 25 \text{ °C}$	-	150	-	mS
Dynamic	characteristics					
$Q_{G(tot)}$	total gate charge	$V_{DS} = -25 \text{ V}; I_D = -200 \text{ mA}; V_{GS} = -5 \text{ V};$	-	0.26	0.35	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.12	-	nC
Q_{GD}	gate-drain charge		-	0.09	-	nC
C _{iss}	input capacitance	$V_{DS} = -25 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$	-	24	36	pF
C _{oss}	output capacitance	T _j = 25 °C	-	4.5	-	pF
C _{rss}	reverse transfer capacitance		-	1.3	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = -30 \text{ V}; R_L = 250 \Omega; V_{GS} = -10 \text{ V};$	-	13	26	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega$; $T_j = 25 °C$	-	11	-	ns
t _{d(off)}	turn-off delay time		-	48	96	ns
t _f	fall time		-	25	-	ns
Source-d	rain diode					
V_{SD}	source-drain voltage	$I_S = -115 \text{ mA}; V_{GS} = 0 \text{ V}; T_i = 25 \text{ °C}$	-0.48	-0.85	-1.2	V

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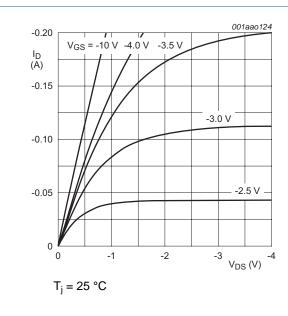
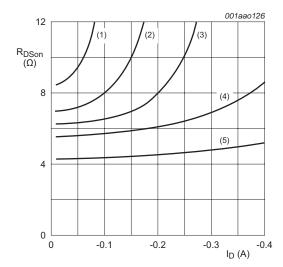


Fig 6. Output characteristics; drain current as a function of drain-source voltage; typical values



 $T_i = 25 \, ^{\circ}C$

(1) $V_{GS} = -3.0 \text{ V}$

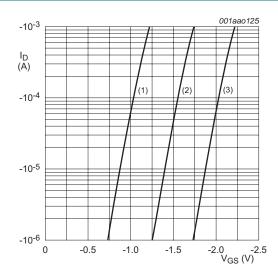
(2) $V_{GS} = -3.5 \text{ V}$

(3) $V_{GS} = -4.0 \text{ V}$

(4) $V_{GS} = -5.0 \text{ V}$

(5) $V_{GS} = -10.0 \text{ V}$

Fig 8. Drain-source on-state resistance as a function of drain current; typical values



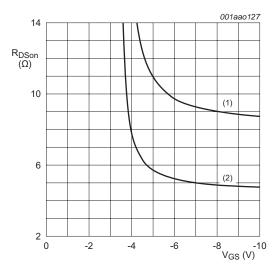
 $T_i = 25 \, ^{\circ}\text{C}; \, V_{DS} = -5 \, \text{V}$

(1) minimum values

(2) typical values

(3) maximum values

Fig 7. Sub-threshold drain current as a function of gate-source voltage

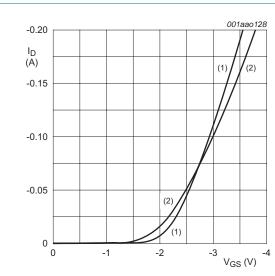


 $I_D = -200 \text{ mA}$

(1) $T_j = 150 \, ^{\circ}C$

(2) $T_i = 25 \, ^{\circ}\text{C}$

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

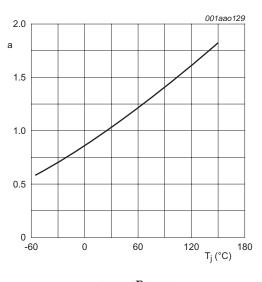


 $V_{DS} > I_D \times R_{DSon}$

(1)
$$T_j = 25 \, ^{\circ}C$$

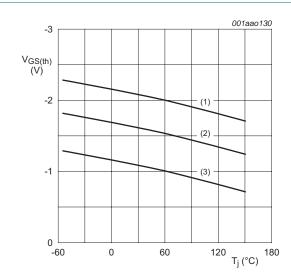
(2)
$$T_i = 150 \, ^{\circ}\text{C}$$

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

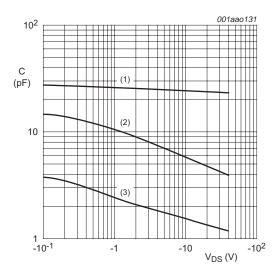
Fig 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values



 $I_D = -0.25 \text{ mA}; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig 12. Gate-source threshold voltage as a function of junction temperature

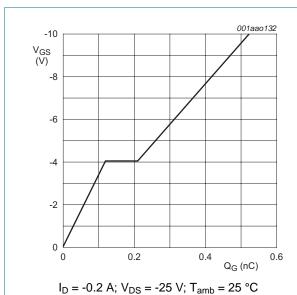


 $f = 1 MHz, V_{GS} = 0 V$

- (1) C_{iss}
- (2) C_{oss}
- (3) C_{rss}

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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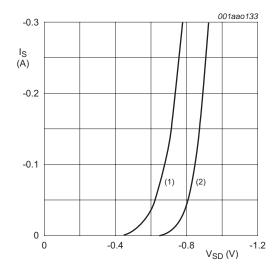


V_{GS}(pl)
V_{GS}(th)
V_{GS}
Q_{GS1} Q_{GS2}
Q_{GS} Q_G(tot)
003aaa508

Fig 14. Gate-source voltage as a function of gate

Gate-source voltage as a function of gate charge; typical values

Fig 15. Gate charge waveform definitions



 $V_{GS} = 0 V$

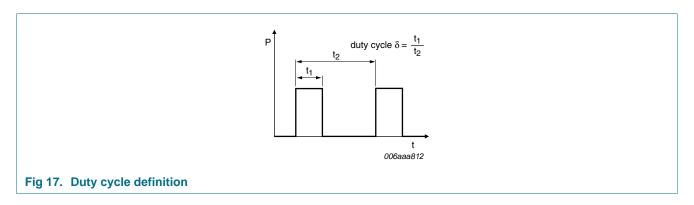
(1) $T_j = 150 \, ^{\circ}\text{C}$

(2) $T_j = 25 \, ^{\circ}C$

Fig 16. Source current as a function of source-drain voltage; typical values

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8. Test information



8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

9. Package outline

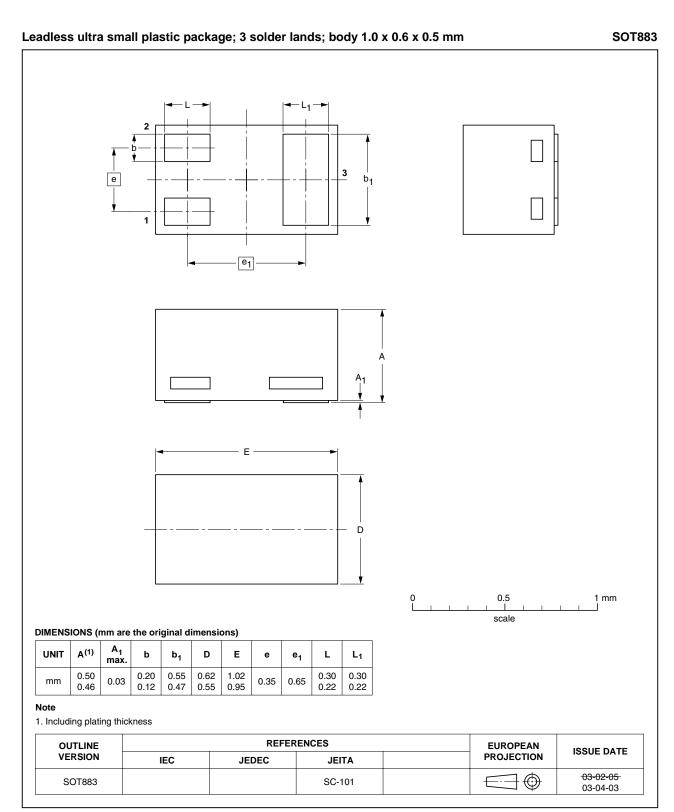
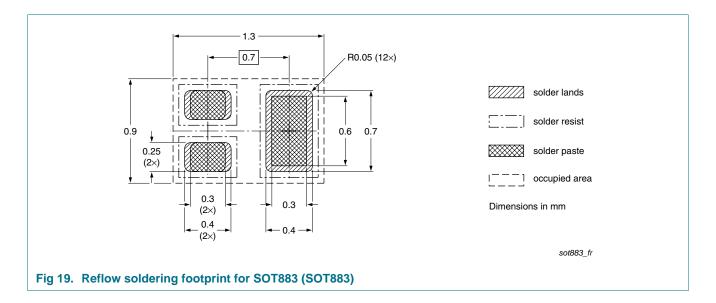


Fig 18. Package outline SOT883 (SOT883)

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10. Soldering



50 V, 230 mA P-channel Trench MOSFET

11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BSS84AKM v.1	20110523	Product data sheet	-	-

50 V, 230 mA P-channel Trench MOSFET

12. Legal information

12.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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